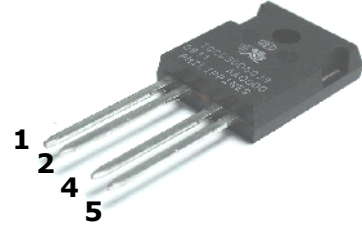
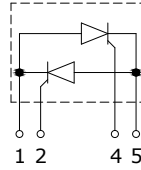


**Silicon Controlled Rectifier, 1200/ 20A  
 In Isolated TO247 Package**

- Pb-free lead finish; RoHS compliant


**MAXIMUM RATINGS (per SCR), at  $T_j = 25^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Value	Units
Average on-state current $T_c = 85^\circ\text{C}$ , $T_j = 125^\circ\text{C}$	$I_{T(AV)}$	20	A
Non-repetitive surge peak on-state current $T_j = 125^\circ\text{C}$ , $t_p = 10\text{ ms}$	$I_{TSM}$	340	
$I^2t$ value for fusing $T_j = 125^\circ\text{C}$ , $t_p = 10\text{ ms}$	$I^2t$	574	$\text{A}^2\text{s}$
Rate of rise of on-state current $T_j = 125^\circ\text{C}$	$di/dt$	200	$\text{A}/\mu\text{s}$
Peak gate current $T_j = 125^\circ\text{C}$	$I_{GM}$	2	A
Maximum repetitive peak off-state voltage $I_R = 100\mu\text{A}$	$V_{DRM}$	1200	V
Maximum repetitive reverse voltage $I_R = 100\mu\text{A}$	$V_{RRM}$	1200	
Operating junction and storage temperature	$T_j, T_{stg}$	-40... +125	$^\circ\text{C}$

**Thermal and Isolation Characteristics (per SCR)**

Parameter	Symbol	Max. Value	Units
<b>Characteristics</b>			
Thermal resistance, junction to case	$R_{thJC}$	1.0	K/W
Thermal resistance, junction to ambient	$R_{thJA}$	40	
Isolation voltage, RMS (measured between terminals and case)	$V_{iso}$	2500	V

**Electrical Characteristics (per SCR), at  $T_j = 25^\circ\text{C}$ , unless otherwise specified**

Symbol	Test Conditions	Value			Unit
		Min.	Typ.	Max.	
$I_{GT}$	Anode supply = 6V	-	60	-	mA
$V_{GT}$		-	1.3	-	
$V_{GD}$	$T_j = 125^\circ\text{C}$	-	0.25	-	V
$I_{GD}$		-	2.0	-	
$I_H$	$T_j = 125^\circ\text{C}$ , Anode supply = 6V	-	125	-	mA
$I_L$		-	180	-	
$dV/dt$	$T_j = 125^\circ\text{C}$	-	200	-	$\text{V}/\mu\text{s}$
$V_{TM}$	$I_F = 30\text{A}$	-	1.3	-	V
$V_{TO}$		-	1.03	-	
$R_f$	$T_j = 125^\circ\text{C}$	-	10.5	-	$\text{m}\Omega$
$t_q$		-	100	-	$\mu\text{s}$

**Package Outline Drawing**

